



Express Mail No. EV 346 811 082 US

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

## In re Application of: Bruno GHYSELEN et al.

Confirmation No. 2491

**Application No.: 10/784,017**

## **Group Art Unit:**

Filing Date: February 20, 2004

**Examiner:**

**For: METHOD FOR FORMING A RELAXED OR  
PSEUDO-RELAXED USEFUL LAYER ON A  
SUBSTRATE**

Atty. Docket No.: 4717-10200

## **SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, enclosed are copies of (8) references for the Examiner's review and consideration. These references were cited in the specification of the application and in preliminary search report and a copy is enclosed..

These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee or certification is believed to be due for this submission since the references are being submitted concurrent with the filing of this application. Should any fees be required, however, please charge such fees to **Winston & Strawn** Deposit Account No. 50-1814.

Respectfully submitted,

Date: 6/11/09

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## Enclosures



**LIST OF REFERENCES CITED BY APPLICANT**  
(Use several sheets if necessary)

ATTY. DOCKET NO.:	APPLICATION NO.:
4717-10200	10/784,017
APPLICANT:	
Bruno GHYSELEN et al.	
FILING DATE:	GROUP:
February 20, 2004	

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	5,461,243	10/1995	Ek et al.	257	190	
	AB	6,352,942 B1	3/2002	Luan et al.	438	770	
	AC	2002/0072130	6/2002	Cheng et al.	438	10	
	AD						
	AE						
	AF						
	AG						
	A1						

**FOREIGN PATENT DOCUMENTS**

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AJ							
	AK							
	AL							

**OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)**

	AM	B. Holländer et al., "Strain relaxation of pseudomorphic Si <sub>x</sub> Ge <sub>y</sub> /Si(100) heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication", Nuclear Instruments and Methods in Physics Research B 175-177 (2001) 357-367 (2001)
	AN	K.D. Hobart et al. "Complaint Substrates: A Comparative Study of the Relaxation Mechanisms of Strained Films Bonded to High and Low Viscosity Oxides", Electronic Materials, Vol. 29, No. 7 , pp. 897-900 (2000)
	AO	Friedrich Schäffler, "High-mobility Si and Ge structures", Semicond. Sci. Technol., Vol. 12, pp.1515-1548 (1997)
	AP	Q. Y. Tong et al "Extracts of "Semi-conductor on wafer bonding", Science and Technology, Interscience Technology, Wiley Interscience publication, Johnson Wiley & Sons, Inc.
	AQ	J.P. Collinge, "Silicon-on-insulator technology", Materials to VLSI, 2nd Edition", Kluwer Academic Publisher, pp. 50-51.

EXAMINER	DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.